		cture-wise bro	еакир				
<b>Course Code</b>	19M21PH216	Semester: Even Semester: IV Session: 2023-2024					
		Month from: January-June					
Course Name	Advanced Condens	Advanced Condensed Matter Physics-2					
Credits	04		Contact I	Hours		04	

#### <u>Detailed Syllabus</u> Lecture-wise Breakun

Faculty	Coordinator(s)	Ashish Bhatnagar
(Names)	Teacher(s) (Alphabetically)	Ashish Bhatnagar

COURSE	OUTCOMES	COGNITIVE LEVELS
C230-5.1	Understand the Physics behind the defects in materials	Remember Level (C1)
C230-5.2	Understand the role of defects in determining properties of materials	Understand Level (C2)
C230-5.3	Develop knowledge of conception or notion involved in various theories and models studied in this course	Apply Level (C3)
C230-5.4	Applying various experimental method/tools to understand the defects in solids	Apply level (C4)

Module No.	Title of the Module	Topics in the Module	No. of Lectures for the module
1.	Defects and Diffusion in solids	Introduction to Defects. Equilibrium Point defects, Vacancy Formation, Vacancy Concentration Determination, Self-Interstitial Defects, Frenkel Defects, Extrinsic Defects, Equilibrium Concentration of Defects, Thermodynamics of Defects, Interstitial Diffusion. Non-Steady State Diffusion, Self Diffusion,, Diffusion Along Defects	12

2	Extended	l Defects	Dislocations, Edge Dislocations, Mixed Dislocations, unit and Partial Disclocations, Multiplications of Dislocations, Interaction of Dislocations and Point Defects: Dislocations Loops, Dislocation climb, Decoration of Dislocation, Internal Boundaries, Low angle Boundaries, Twin Boundaries, Antiphase Boundaries	12
3	Defects I	Dynamics	Dislocation in FCC, HCP and BCC, Partial Dislocation, Stacking Fault, Burger Vector and its properties	8
4	· Observat Defects i	ion of n Solids	Experimental method of detecting dislocations and sta cking faults, Electron Microscopy: Kinematical theory of diffraction contrast and lattice imaging.	8
			Total number of Lectures	40
Eval	uation Criteria	ı		
Com T1 T2 End S TA Tota	i <b>ponents</b> Semester Examin	ation	Maximum Marks 20 20 35 25 [Attendance (05 M), Class Test, Quizzes, etc (06 M), Assi mode (10 M), and Internal assessment (04 M)]] 100	gnments in PBL
Reco book	ommended Rea as, Reference Bo	i <b>ding mate</b> boks, Journ	erial: Author(s), Title, Edition, Publisher, Year of Publicate als, Reports, Websites etc. in the IEEE format)	tion etc. ( Text
1.	Richard J. D. 7	Tilley, "De	fects in Solids", John Wiley & Sons, Inc.	
2	Weertman J. a	and Weertn	nan J. R. "Elementary Dislocation Theory"	
3	Anderson P.M	. , Hirth J.I	P., Lothe J., "Theory of Dislocations" 3rd Edition	
4	Hirsch, P.B., "	Electron M	licroscopy of Thin Crystals"	

**Project based learning:** Students would work on a project of their choice in the field of defects in materials. In this project student will identify the materials with a defect and then apply various experimental techniques like electron microscopy, X-Ray Diffraction to visualize/calculate the various parameter related to defects etc. The student will also compare the theory proposed about the given defects with their observations through above mentioned experimental techniques. This practice will improve their hands-on practical skill which is one of the main criteria for employability.

# **Detailed Syllabus**

Course Code		19M27PH211	Semester: EVEN		Semester: 4 <sup>th</sup> S		Session: 2023-24	
					n from: J	an to June		
Course N	ame	Dissertation						
Credits		10		Contact Hours	t 20			
Faculty (Names)	y Coordinator(s) Manoj Kumar							
		Teacher(s) (Alphabetically)	Ashish Bh Chhoker	atnagar, N	Javendu	Goswam	ii and Sandeep	
COURSE	URSE OUTCOMES COGN LEVE						COGNITIVE LEVELS	
C250.1	Revie explo techr proje cond	Review the contemporary scholarly literature, activities, and Understanding (C2) (C2) (C2)						
C250.2	Acquire knowledge in the selected field of study. AnalyzeAnalyzevarious feasible methods/techniques of solving a problem toslot a appropriate solution methodology						Analyzing (C4)	
C250.3	Employ latest techniques and software tools to accomplish the proposed objectives. Evaluate/validate obtained results based on evidence and analysis.							
C250.4	Dem comr futur	onstrate the tec nunication skills. I e developments in t	hnical repo llustrate the he selected fi	ort writi significa ield.	ng an nce of	d oral possible	Create Level (C6)	

S.N.	Topics in module
	Identification of the dissertation problem and literature review in the related field
Module 1	and explore experimental and theoretical tools/ techniques/software/hardware.
	Acquire knowledge and analyze various methods/techniques to be used in solving
Module 2	the defined problem and find a suitable methodology.

	Utilize latest techniques/software/hardware tools to achieve the proposed objectives
Module 3	and obtain results. Evaluation/analysis of the obtained results and their
	interpretation.
	Compilation of the results and report writing with ethics (plagiarism less than 10%)
Module 4	and presentation of the dissertation work.

<b>Evaluation Criteria</b>	
Components	Maximum Marks
Day to Day Evaluation	40 (To be awarded by supervisor)
End Semester Evaluation	50 (To be awarded by a panel of 3 examiners)
Special Contribution	10 (To be awarded by a panel of 3 examiners)
Total	100

## **<u>CO-PO and CO-PSO Mapping:</u>**

COs	PO1	PO2	PO3	PSO1
C250.1	1	3		3
C250.2	1	3		3
C250.3	1	3		3
C250.4			3	
Av C250	1	3	3	3

				cture-wise bro	еакир			
Course Co	de	20M22PH2	15	Semester: Eve	en	Semeste	er 4th Session	2023-24
						Month 1	from: Jan to June	•
Course Na	me	Introduction	to Nar	oscience		1		
Credits			3		Contact	Hours	3	3
Faculty		Coordinate	or	Prof. Navend	u Goswam	ni		
(Names)		Teacher		Prof. Navend	u Goswam	ii		
COURSE (	OUTC	COMES		·	COGNIT E LEVE			
C231-1.1	Reca	all basics of n	anoscie	ence and nanom	aterials			Rememberin g (C1)
C231-1.2	Expl	ain various p	n various physical phenomena under the domain of nanoscience $g(C2)$				Understandin g (C2)	
C231-1.3	App	ly the concept	the concept and principles to solve problems related to nanoscience Applying (C3)				Applying (C3)	
C231-1.4	Anal appl:	lyze and exan ication-orient	mine the concepts of nanoscience and nanomaterials for Analyzing (C4)				Analyzing (C4)	
Module	Title	e of the	Торіс	ics in the Module			No. of	
No.	Mod	lule	_					Lectures for
								the module
1.	Intro nano	oduction to oscience	Devel natura Quant nanot Schro D, 2-I Partic	opment of nanoscience and nanotechnology, illy occurring nanomaterials, Introduction to tum Mechanics (with relevance to echnology), Electron confinement using dinger wave equation, Particle confinement in 1- D, 3-D box, Density of states. Potential barrier and le tunneling: Its applications			6	
2.	Proj nano	perties of omaterials	Classi to vol and (optic plasm (super prope Nanor	ification of nan lume ratio, Sur fluctuations), al properties), nons), rparamagnetisn rties of nanon materials (Reac	omaterials face states Semicor Metallic Magnetic n/nanomag naterials, ( tivity etc.)	s, Bulk to s and ene nducting nanopar gnetism), Chemica	Nano, Surface rgy (Reactivity nanoparticles ticles (surface nanoparticles Mechanical Properties of	8
3.	Synt nanc	thesis of omaterials	Top t and C	o Bottom appr Growth, Physic	oach and al Method	Vice Ve ls, Mecha	rsa, Nucleation anical Methods	10

### <u>Detailed Syllabus</u> Lecture-wise Breakup

		(Ball milling and Melt Method), Evaporative methods,	
		CVD and Sputtering, Epitaxial Growth, Chemical	
		Methods (Sol Gel, precipitation, Hydrothermal, Spray),	
		Langmuir-Blodget Method	
4.	Some special	Carbon nanomaterials (Fullerenes, CNT and	10
	nanomaterials	Graphene), Nanomagnetism, Superconducting	
		nanomaterials, Solar materials, Sensing Materials, High	
		mobility and 2-D electron gas materials, Metal- Organic	
_	A	Framework, Porous Materials, Core-Shen Materials,	
5.	Applications of	Energy Applications, SI-based solar cells, DSSC,	0
	nanomateriais	detector Quantum well papostructures for LEDs GaN	
		and its Applications Environmental and Agricultural	
		Medical, space, food and others	
		Total number of Lectures	40
		Total number of Lectures	40
Eval	uation Criteria		
Eval Com	uation Criteria ponents	Maximum Marks	
Eval Com T1	uation Criteria ponents	<b>Maximum Marks</b> 20	
Eval Com T1 T2	uation Criteria ponents	Maximum Marks 20 20	
Eval Com T1 T2 End	uation Criteria ponents Semester Examination	Maximum Marks 20 20 35	
Eval Com T1 T2 End TA	uation Criteria ponents Semester Examination	Maximum Marks 20 20 35 25 [PBL (10 M), 2 Quiz (6 M), Attendance (5 M)	
Eval Com T1 T2 End TA	<b>Luation Criteria</b> <b>Iponents</b> Semester Examination	Maximum Marks 20 20 35 25 [PBL (10 M), 2 Quiz (6 M), Attendance (5 M) and Internal Assessment (4 M)]	
Eval Com T1 T2 End TA TA	uation Criteria ponents Semester Examination	Maximum Marks 20 20 35 25 [PBL (10 M), 2 Quiz (6 M), Attendance (5 M) and Internal Assessment (4 M)] 100	
Eval Com T1 T2 End TA Tota Reco	uation Criteria ponents Semester Examination I mmended Reading mate	Maximum Marks 20 20 35 25 [PBL (10 M), 2 Quiz (6 M), Attendance (5 M) and Internal Assessment (4 M)] 100 erial: Author(s), Title, Edition, Publisher, Year of Publicat	ion etc. (Text
Eval Com T1 T2 End TA Tota Reco	luation Criteria ponents Semester Examination ll pmmended Reading mate as, Reference Books, Journ	Maximum Marks 20 20 35 25 [PBL (10 M), 2 Quiz (6 M), Attendance (5 M) and Internal Assessment (4 M)] 100 prial: Author(s), Title, Edition, Publisher, Year of Publicat als, Reports, Websites etc. in the IEEE format)	ion etc. (Text
Eval Com T1 T2 End TA Tota Reco book	uation Criteria ponents Semester Examination I ommended Reading mate as, Reference Books, Journ Nanostructures and nano	Maximum Marks 20 20 35 25 [PBL (10 M), 2 Quiz (6 M), Attendance (5 M) and Internal Assessment (4 M)] 100 prial: Author(s), Title, Edition, Publisher, Year of Publicat als, Reports, Websites etc. in the IEEE format) materials: synthesis properties and application, Guozhong	ion etc. (Text
Eval Com T1 T2 End TA Tota Reco book	uation Criteria ponents Semester Examination M Semended Reading mate as, Reference Books, Journ Nanostructures and nano college press, London.	Maximum Marks 20 20 35 25 [PBL (10 M), 2 Quiz (6 M), Attendance (5 M) and Internal Assessment (4 M)] 100 prial: Author(s), Title, Edition, Publisher, Year of Publicat als, Reports, Websites etc. in the IEEE format) materials: synthesis properties and application, Guozhong	ion etc. (Text 5 Cao, Imperial
Eval Com T1 T2 End TA Tota Reco book	uation Criteria ponents Semester Examination d mmended Reading mate s, Reference Books, Journ Nanostructures and nano- college press, London. Introduction to nanotechr	Maximum Marks 20 20 35 25 [PBL (10 M), 2 Quiz (6 M), Attendance (5 M) and Internal Assessment (4 M)] 100 erial: Author(s), Title, Edition, Publisher, Year of Publicat als, Reports, Websites etc. in the IEEE format) materials: synthesis properties and application, Guozhong mology, Charles Poole et al J John Wiley & Sons, Singapor	ion etc. (Text 5 Cao, Imperial re.

**Project Based Learning:** Each student will be given a small project in which they will carry out the theoretical or experimental work on the selected topic from energy applications, Si-based solar cells, DSSC, hydrogen Storage, battery and fuel cells, photo detector, quantum well nanostructures for LEDs, GaN and its applications, environmental and agricultural medical, space, food and others. Synthesis part for the experimental project will be carried out in the laboratory facility of the Department and the theoretical part will be kept feasible for the student to execute. This project will make them prepared for industry jobs in the nanomaterial industry as well as for higher studies.

### <u>Detailed Syllabus</u> Lecture-wise Breakup

Course Code		20M22PH216		Semester: Even	Semester: IV	: IV Session: 2023-2024		
Course Norre		Month: January to June						
Course Name		Design and Fabrication of Solar Cells						
Credits		Coordinator	3 Contact Hours 3					
Faculty (Names)		Coordinator(s) Manoj Kumar   Toochor(c) Image: State Stat						
(Inallies)		Teacher(s)					COCNIT	WF
COURSE OUTC		COMES					LEVELS	
C231-2.1	Class resou	sify the various types of renewable and nonrenewable energy Understan urces and explain the working of photovoltaic devices. (C2)					nd Level	
C231-2.2	Demo photo	nonstrate the basic principles to design, model and fabricate (C2)					d Level	
C231-2.3	Ident: vario	tify challenges and apply strategies to optimize performance of Apply Lev (C3)						/el
C231-2.4	Analy modu	yze Solar PV module, mismatch parameter and rating of PV Analyze L ule (C4)					level	
C231-2.5	Evalu batter	uate the performance of various stand-alone PV systems with ery and AC and DC loadEvaluate Le (C5)					evel	
Module	Title	of the	Top	oics in the Module				No. of
No.	Mod	ule						Lecture
								s for the
			Energy instantiant and the second sec					module
1.	Revie	ew	ener	rgy sources, Solar Ene	gy			02
2.	Solar funda	cell mentals	Sem reco illun (Vo and	niconductor materia ombination, p-n junc mination, Current-Vo c), short circuit curre voltage and Efficienc	s, carriers generation and ion diode, p-n junction under tage (I-V), open circuit voltage t ( $I_{SC}$ ), Maximum power, current r, Quantum Efficiency			08
3.	Solar and T	cell Design echnologies	Upp desi base (CIC amo Emo sens pero	ber limits of cell parar lign, design for high $I_{sc}$ ed solar cell technolog GS, microcrystalline orphous Si thin film so erging solar cell techr sitized solar cell (DSS ovskite soar cell.	meters, loses in solar cell, solar cell <sub>c</sub> , $V_{oc}$ , FF, Production of Si, Si wafer gy, thin film solar cell technologies and polycrystalline Si solar cells, olar cells), multijunction solar cells, nologies: organics solar cells, Dye- SC), GaAs solar cell, Introduction of			12
4.	Fabri chara solar	cation and cterization of cells	Fab text met Cha mea	rication of Si so urization, diffusion, e al print, back conta tracterization: Solar S usurement	ar cells: Surface preparation, ching, cleaning, oxide passivation, ct print, firing/sintering, testing, mulators and Quantum Efficiency			10

5	Solar Photovoltaic Applications	Solar Photovoltaic Modules, Series/parallel connection, mismatch, bypass diode, Effect of temperature, Balance of system- BOS (Inverters, Controllers, Wiring, Batteries), Photovoltaic system, Standalone system, Grid connected system, Hybrid system, Designing of PV system, Estimating PV system size and cost, Photovoltaic safety.	08					
		Total number of Lectures	40					
Evaluation Criteria								
Components Maximum Marks								
T1		20						
T2		20						
End Semester Examination		35						
ТА		25 [Attendance (5 M), Class Test, Quizzes, <i>etc</i> (6 M), Assignments in PBL mode (10 M), and Internal assessment (4 M)]						
Tota	1	100						
Recommended Reading material: Author(s), Title, Edition, Publisher, Year of Publication etc. (Text								
book	books, Reference Books, Journals, Reports, Websites etc. in the IEEE format)							
1.	Tom Markvart and Luis Castaner, "Solar Cells: Materials, Manufacture and Operations," Elsevier, 2006							
2.	Stuart R. Wenhem, Martin A. Green, M.E. Watt, "Applied Photovoltaics," Earthscan, 2007							
3.	Jenny Nelson, "The Physics of Solar Cells" Imperial college press," Aatec publications, 1995.							
4.	C S Solanki, "Solar Photovoltaics: Fundamentals, Technologies and Applications", PHI, 2015							
5.	Richard J. Komp "Practical Photovoltaics: Electricity from Solar Cells", Aatec Publications, 1990							

**Project based learning:** Students will have to submit a working project/model based on design & fabrication of solar cells. This will enhance their basic understanding of solar cell, issues in designing & fabrication of solar cells and their applications. At the end of the semester, students will be asked to submit and present their projects on the basis of which PBL marks will be awarded.